

# **STPS3100B(-TR)**

# HIGH VOLTAGE POWER SCHOTTKY RECTIFIER

#### MAIN PRODUCT CHARACTERISTICS

I <sub>F(AV)</sub>	3 A
V <sub>RRM</sub>	100 V
V <sub>F</sub> (max)	0.59 V

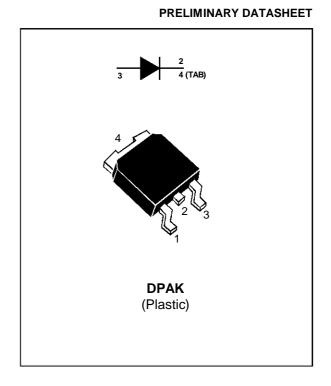
#### **FEATURES AND BENEFITS**

- NEGLIGIBLE SWITCHING LOSSES
- LOW FORWARD DROP VOLTAGE
- LOW CAPACITANCE
- HIGH REVERSE AVALANCHE SURGE CAPABILITY
- TAPE AND REEL OPTION: -TR

#### **DESCRIPTION**

High voltage Schottky rectifier suited for Switch Mode Power Supplies and other Power Converters.

Packaged in DPAK, this device is intended for use in medium voltage operation, and particularly, in high frequency circuitries where low switching losses are required.



### **ABSOLUTE MAXIMUM RATINGS**

Symbol	Parameter	Value	Unit	
V <sub>RRM</sub>	Repetitive Peak Reverse Voltage		100	V
I <sub>F(RMS)</sub>	RMS Forward Current	6	Α	
l <sub>F(AV)</sub>	Average Forward Current	Tcase = 120°C δ = 0.5	3	А
I <sub>FSM</sub>	Surge Non Repetitive Forward Current	tp = 10 ms Sinusoidal	50	А
I <sub>RRM</sub>	Repetitive Peak Reverse Current	tp = 2 μs F = 1KHz	1	А
T <sub>stg</sub>	Storage Temperature Range	- 65 to + 150	°C	
Tj	Max. Junction Temperature	125	°C	
dV/dt	Critical Rate of Rise of Reverse Voltage	1000	V/μs	

August 1995 - Ed : 1B

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## THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
R <sub>TH</sub> (j-c)	Junction to Case Thermal Resistance	3.5	°C/W

## STATIC ELECTRICAL CHARACTERISTICS

Symbol	Tests Conditions	Tests Conditions		Min.	Тур.	Max.	Unit
I <sub>R</sub> *	Reverse leakage Current	Tj = 25°C	V <sub>R</sub> = 100 V			30	μΑ
		Tj = 125°C			4.5	10	mA
V <sub>F</sub> **	Forward Voltage drop	Tj = 25°C	I <sub>F</sub> = 3 A			0.65	V
		Tj = 125°C	I <sub>F</sub> = 3 A		0.55	0.59	

Pulse test: \* tp = 5 ms, duty cycle < 2 %

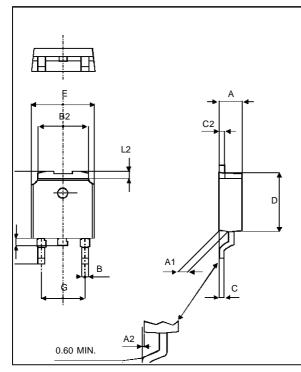
\*\* tp =  $380 \,\mu s$ , duty cycle < 2%

To evaluate the maximum conduction losses use the following equation :

 $P = 0.49 \text{ x } I_{F(AV)} + 0.035 I_{F}^{2}_{(RMS)}$ 

# PACKAGE MECHANICAL DATA





	DIMENSIONS					
REF.	Millimeters			Inches		
	Min.	Тур.	Max	Min.	Тур.	Max.
Α	2.20		2.40	0.086		0.094
A1	0.90		1.10	0.035		0.043
A2	0.03		0.23	0.001		0.009
В	0.64		0.90	0.025		0.035
B2	5.20		5.40	0.204		0.212
С	0.45		0.60	0.017		0.023
C2	0.48		0.60	0.018		0.023
D	6.00		6.20	0.236		0.244
Е	6.40		6.60	0.251		0.259
G	4.40		4.60	0.173		0.181
Н	9.35		10.10	0.368		0.397
L2		0.80			0.031	
L4	0.60		1.00	0.023		0.039
V2	0°		8°	0°		8°

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